

/ Descriptions

TO-252 N MOS

N-CHANNEL MOSFET in a TO-252 Plastic Package.

/ Features

 $V_{DS}=500V$ $I_D=7A$ $R_{DS(ON)}@10V \leq 1.5\Omega$ (Typ. 1.2Ω)

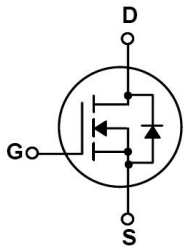
Fast Switching.

HF Product.

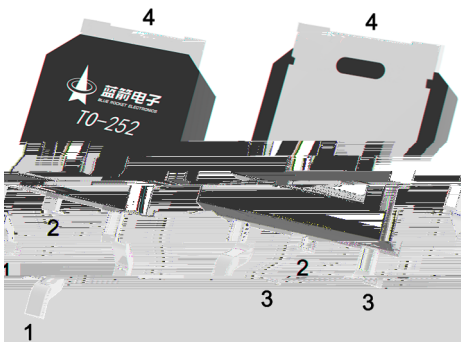
/ Applications

These devices are well suited for power switch circuit of adaptor and charger, intergrate fast recovery diode.

/ Equivalent Circuit



/ Pinning



PIN1 G

PIN 2 D

PIN 3 S

PIN 4 D

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	500	V
Drain Current	$I_D(T_c=25)$	7	A
Drain Current - Pulsed	I_{DM}	28	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	392	mJ
Avalanche Current	I_{AS}	8.4	A
Power Dissipation	$P_D(T_c=25)$	50	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	
Junction to Ambient	$R_{\theta JA}$	110	/W
Junction to Case	$R_{\theta JC}$	2.5	/W

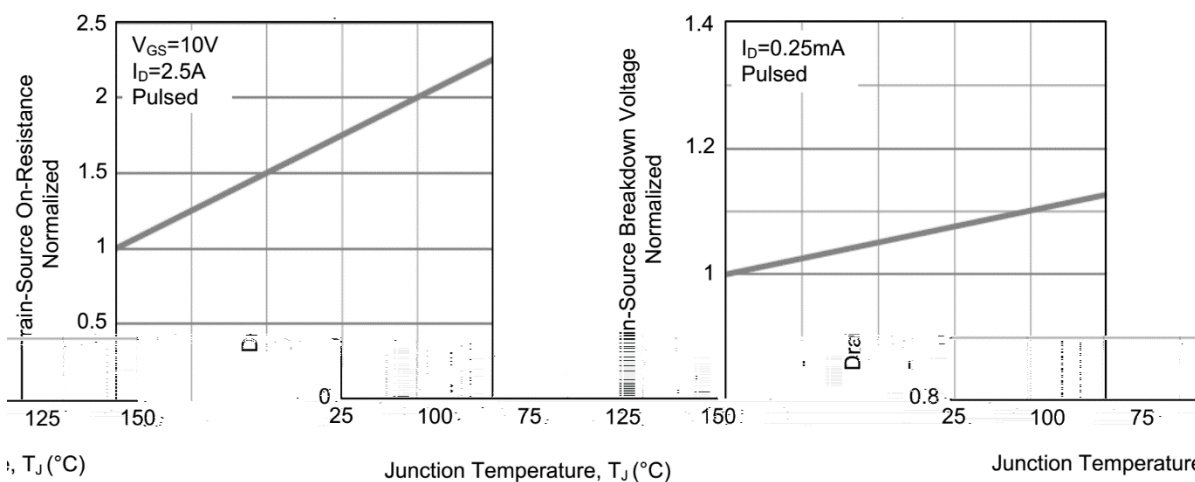
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\mu A$	500	554		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=500V$ $V_{GS}=0V$			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0	2.9	4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=3.0A$		1.2	1.5	Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1.0A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		570		pF
Output Capacitance	C_{oss}			62		
Reverse Transfer Capacitance	C_{rss}			5.5		
Total Gate Charge	Q_G	$V_{DS}=400V$ $I_D=7.0A$ $V_{GS}=10V$		30		nC
Gate-Source Charge	Q_{GS}			12.5		
Gate-Drain Charge	Q_{GD}			5.4		

/ Electrical Characteristics(Ta=25)

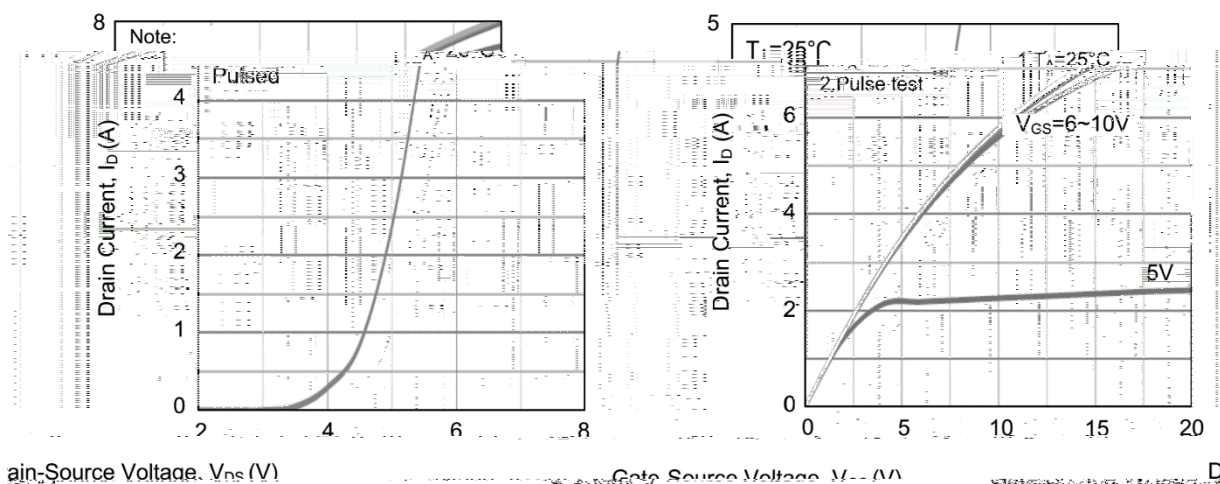
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=100V$ $I_D=7.0A$ $V_{GS}=10V$ $R_G=25\Omega$		11		ns
Turn-On Rise Time	t_r			17.5		
Turn-Off Delay Time	$t_{d(off)}$			53		
Turn-Off Fall Time	t_f			32		
Maximum Continuous Drain-Source Diode Forward Current	I_S				7	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				28	A
Reverse Recovery Time	t_{rr}	$V_{GS}=0V$ $I_S=7.0A$ $dI_F/dt=100 A/\mu s$		90		ns
Reverse Recovery Charge	Q_{rr}			250		nC

/ Electrical Characteristic Curve



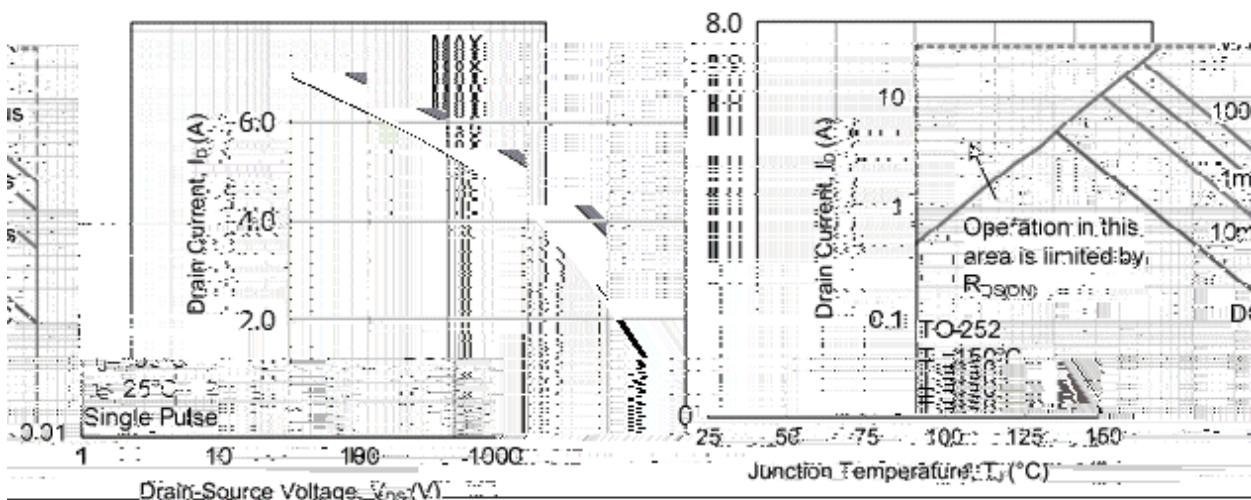
1. Drain-Source On-Resistance vs. Junction Temperature

2. Breakdown Voltage vs. Junction Temperature



3. Drain Current vs. Drain-Source Voltage

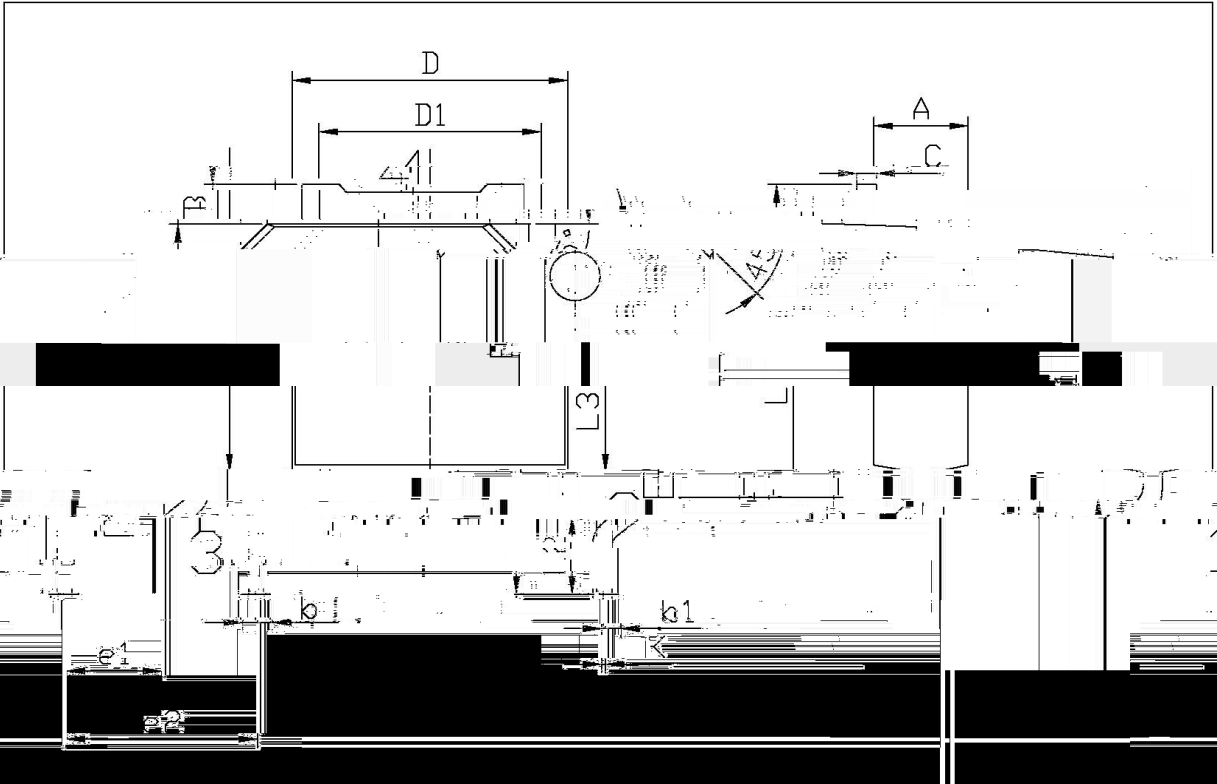
4. Drain Current vs. Gate-Source Voltage



5. Safe Operating Area

6. Drain Current vs. Junction Temperature

/ Package Dimensions

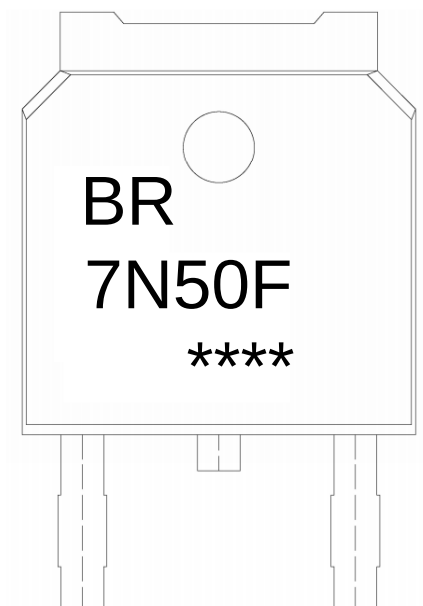


单位: mm

Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min	Max	Symbol	Min	Max
E	5.95	6.25	A	2.20	2.40
e1	2.24	2.34	B	0.95	1.25
L1	9.85	10.35	b1	0.45	0.55
C	0.45	0.55	D	6.45	6.75
3	0.60	0.90	D1	5.10	
5.50	0.00	0.10			

T0=252

/ Marking Instructions



BR

Note:

BR: Company Code

7N50F: Product Type Code

****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245 5

5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec. Temp.:260±5℃ Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box